

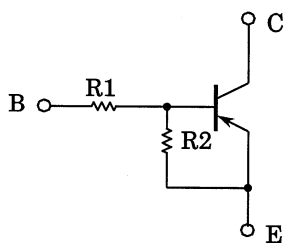
TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

RN2321A,RN2322A,RN2323A,RN2324A RN2325A,RN2326A,RN2327A

Switching, Inverter Circuit, Interface Circuit
And Driver Circuit Applications

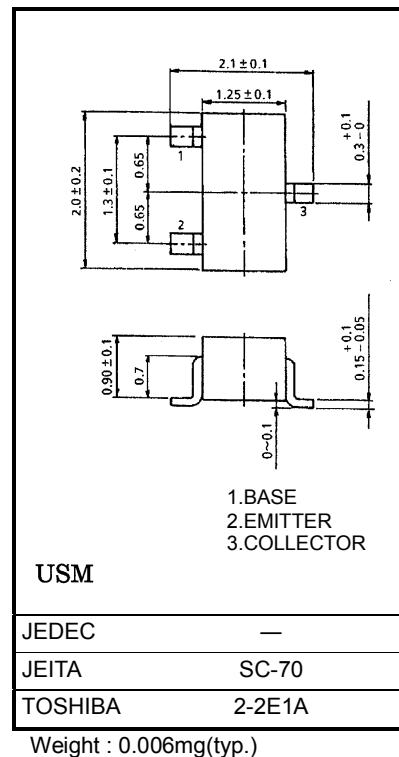
- High current driving is possible.
- Since bias resistors are built in the transistor, the miniaturization of the apparatus by curtailment of the number of parts and laborsaving of an assembly are possible.
- Many kinds of resistance value are lined up in order to support various kinds of circuit design.
- Complementary to RN1321A~RN1327A
- Low $V_{CE(sat)}$ enable to be low power dissipation on high current driving.

Equivalent Circuit And Bias Resistance Values



Type No.	R1 (k Ω)	R2 (k Ω)
RN2321A	1	1
RN2322A	2.2	2.2
RN2323A	4.7	4.7
RN2324A	10	10
RN2325A	0.47	10
RN2326A	1	10
RN2327A	2.2	10

Unit in mm

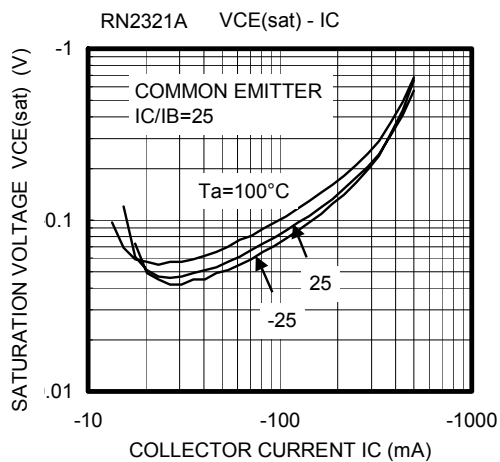
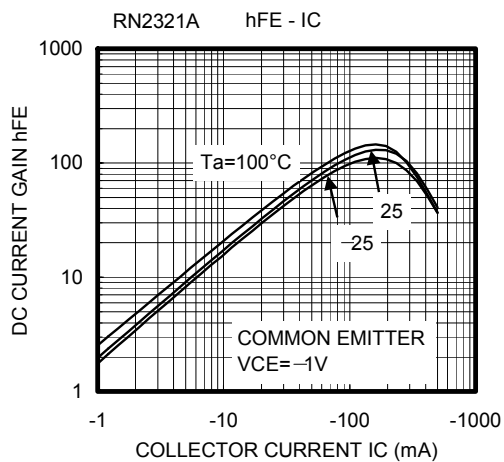
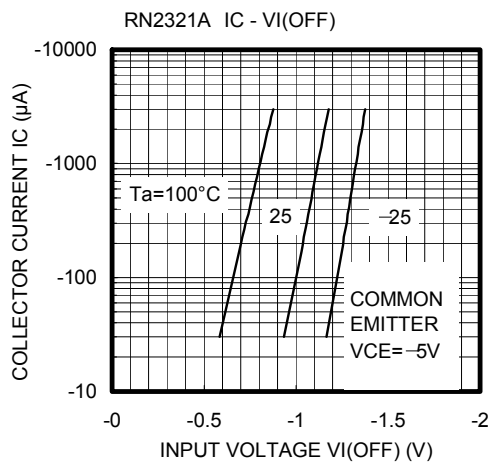
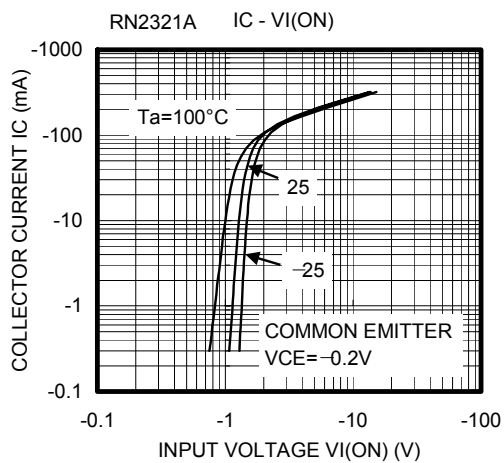


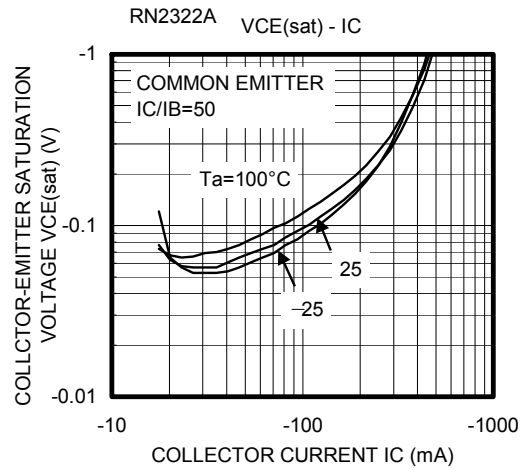
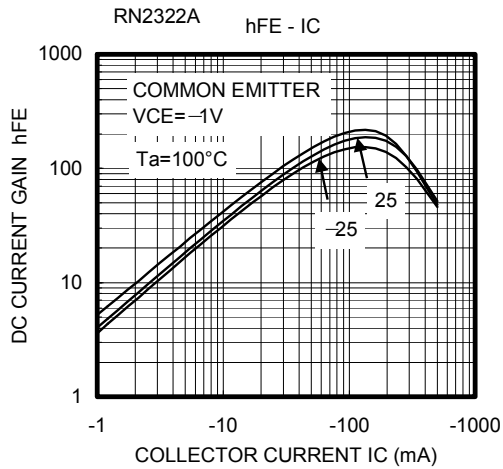
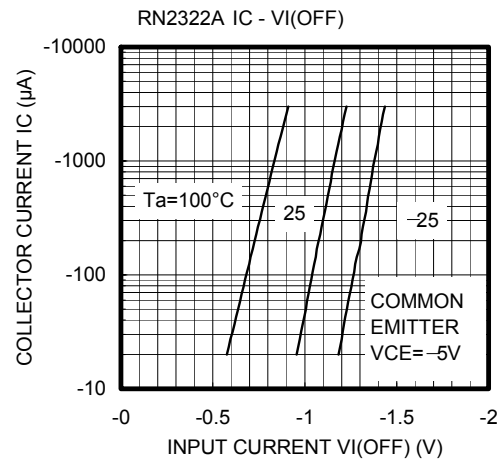
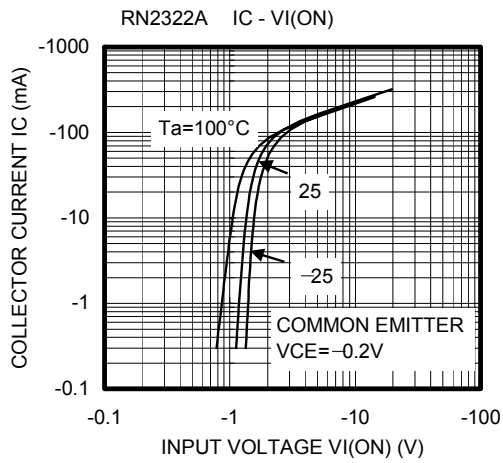
Maximum Ratings (Ta = 25°C)

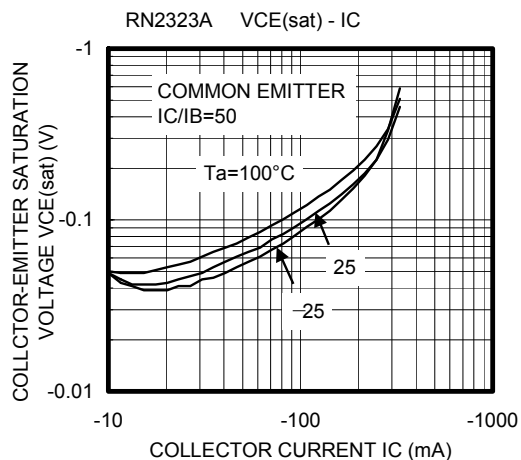
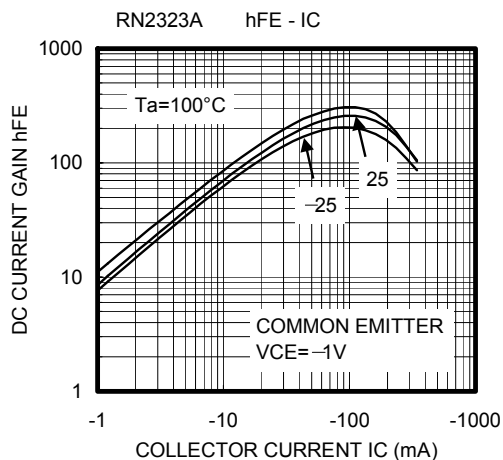
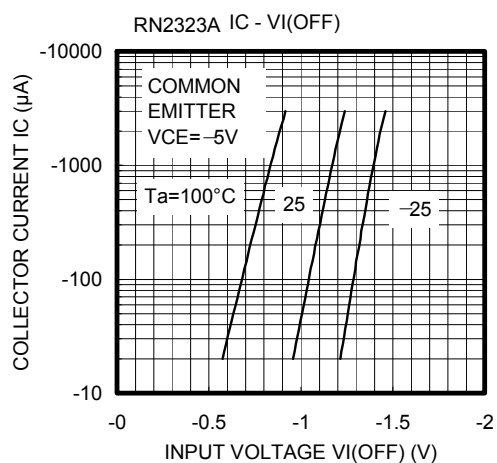
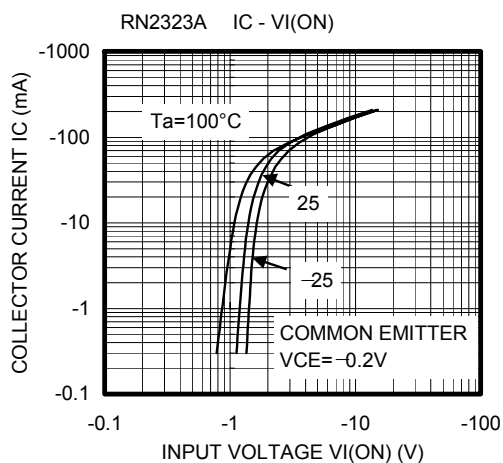
Characteristic		Symbol	Rating	Unit
Collector-base voltage	RN2321A~2327A	V _{CBO}	−15	V
Collector-emitter voltage		V _{CEO}	−12	V
Emitter-base voltage	RN2321A~2324A	V _{EBO}	−10	V
	RN2325A, 2326A		−5	
	RN2327A		−6	
Collector current	RN2321A~2327A	I _C	−500	mA
Collector power dissipation		P _C	100	mW
Junction temperature		T _j	150	°C
Storage temperature range		T _{stg}	−55~150	°C

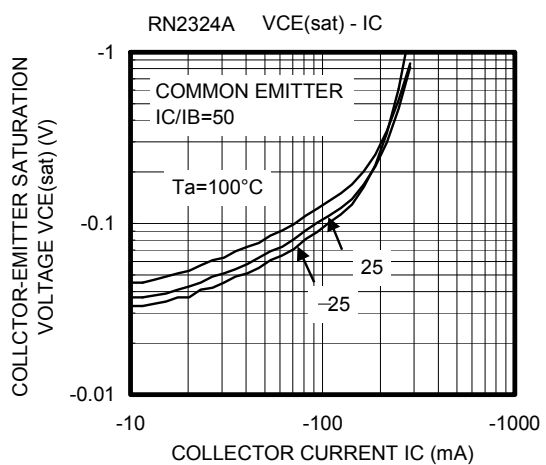
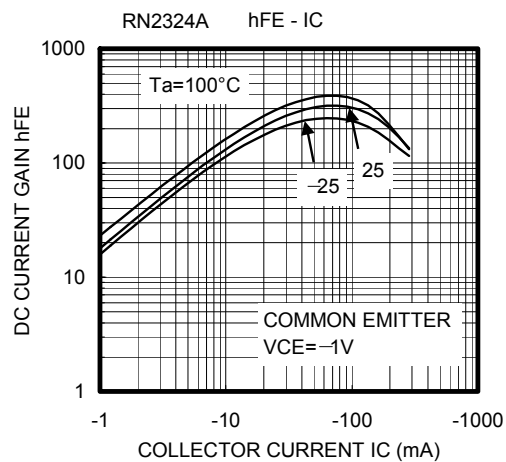
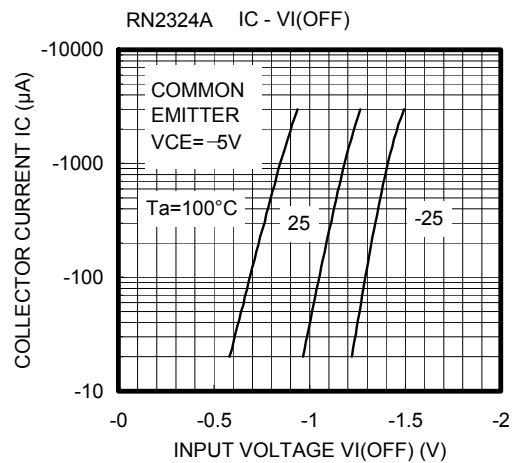
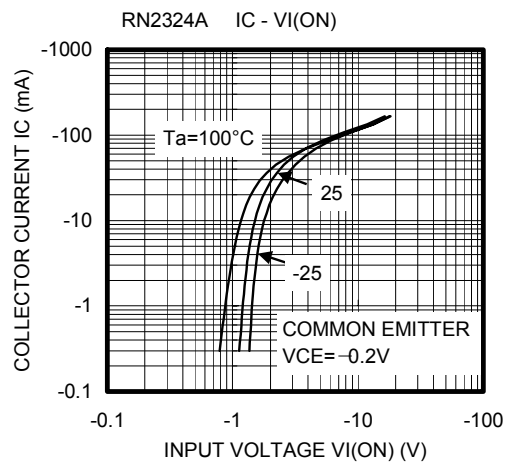
Electrical Characteristics (Ta = 25°C)

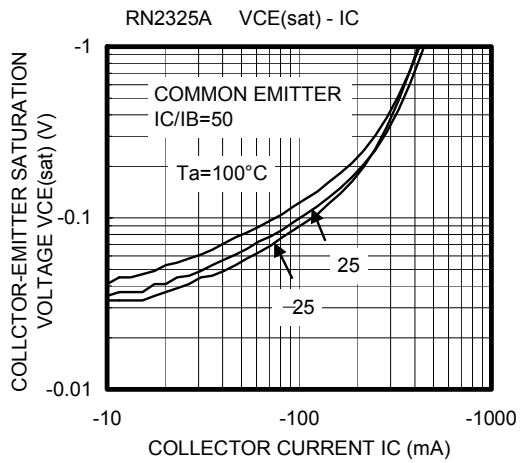
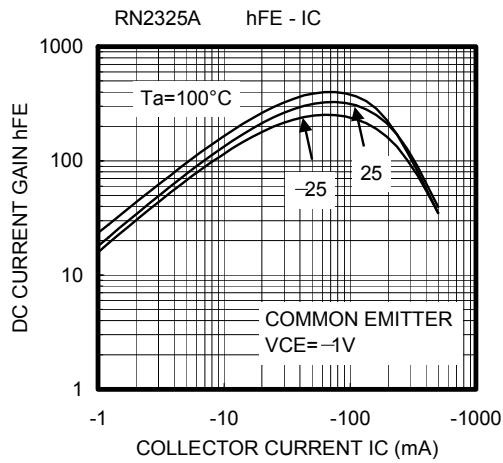
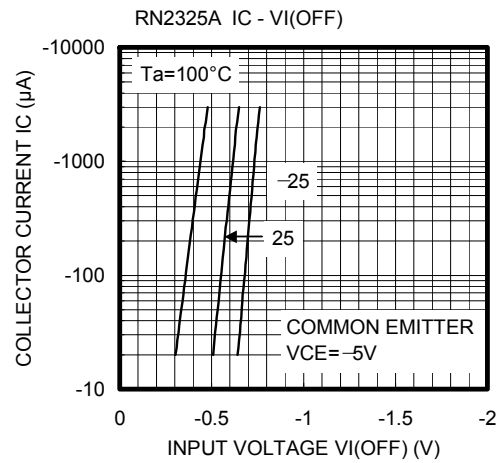
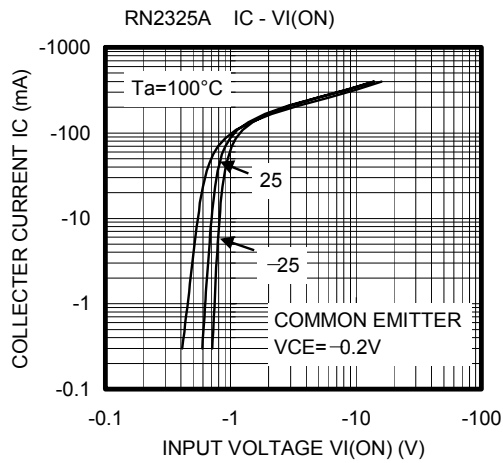
Characteristic		Symbol	Test Circuit	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	RN2321A~2327A	I_{CBO}	—	$V_{CB} = -15V, I_E = 0$	—	—	-100	nA
		I_{CEO}		$V_{CE} = -12V, I_B = 0$	—	—	-500	
Emitter cut-off current	RN2321A	I_{EBO}	—	$V_{EB} = -10V, I_C = 0$	-3.85	—	-7.14	mA
	RN2322A				-1.75	—	-3.25	
	RN2323A				-0.82	—	-1.52	
	RN2324A				-0.38	—	-0.71	
	RN2325A			$V_{EB} = -5V, I_C = 0$	-0.365	—	-0.682	
	RN2326A				-0.35	—	-0.65	
	RN2327A			$V_{EB} = -6V, I_C = 0$	-0.378	—	-0.703	
DC current gain	RN2321A	h_{FE}	—	$V_{CE} = -1V, I_C = -50mA$	35	—	—	
	RN2322A				65	—	—	
	RN2323A				100	—	—	
	RN2324A				140	—	—	
	RN2325A				140	—	—	
	RN2326A				140	—	—	
	RN2327A				140	—	—	
Collector-emitter saturation voltage	RN2321A	$V_{CE(sat)}$	—	$I_C = -50mA, I_B = -2mA$	—	—	-0.25	V
	RN2322A~2327A			$I_C = -50mA, I_B = -1mA$				
Input voltage (ON)	RN2321A	$V_{I(ON)}$	—	$V_{CE} = -0.2V, I_C = -50mA$	-1.0	—	-2.4	V
	RN2322A				-1.1	—	-2.7	
	RN2323A				-1.3	—	-3.5	
	RN2324A				-1.5	—	-5.2	
	RN2325A				-0.5	—	-1.2	
	RN2326A				-0.6	—	-1.4	
	RN2327A				-0.7	—	-1.9	
Input voltage (OFF)	RN2321A~2324A	$V_{I(OFF)}$	—	$V_{CE} = -5V, I_C = -0.1mA$	-0.8	—	-1.4	V
	RN2325A, 2326A				-0.4	—	-0.8	
	RN2327A				-0.5	—	-1.0	
Transition frequency	RN2321A~2327A	f_T	—	$V_{CE} = -5V, I_C = -20mA$	—	200	—	MHz
Collector Output capacitance	RN2321A~2327A	C_{ob}	—	$V_{CB} = 10V, I_E = 0, f = 1MHz$	—	5	—	pF
Input resistor	RN2321A	R1	—	—	0.7	1	1.3	kΩ
	RN2322A				1.54	2.2	2.86	
	RN2323A				3.29	4.7	6.11	
	RN2324A				7	10	13	
	RN2325A				0.329	0.47	0.611	
	RN2326A				0.7	1	1.3	
	RN2327A				1.54	2.2	2.86	
Resistor ratio	RN2321A~2324A	R1/R2	—	—	0.85	1.0	1.15	
	RN2325A				0.040	0.047	0.054	
	RN2326A				0.085	0.1	0.115	
	RN2327A				0.187	0.220	0.253	

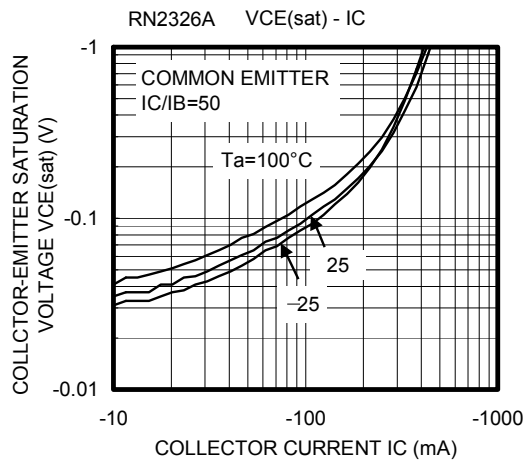
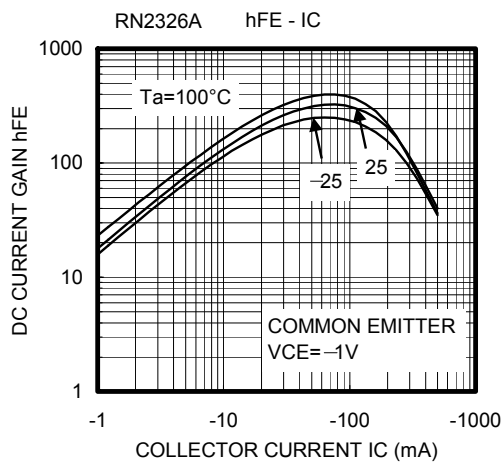
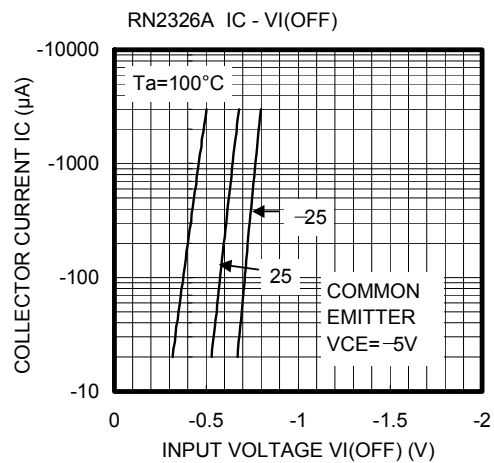
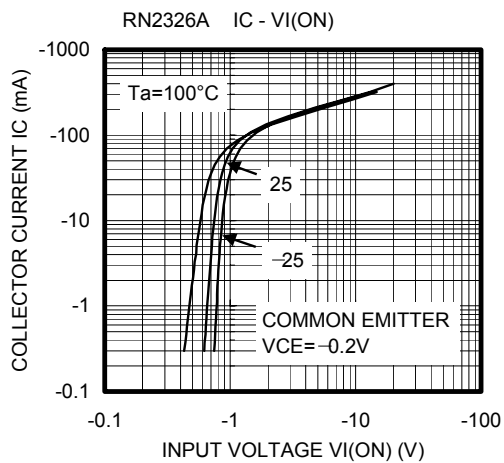


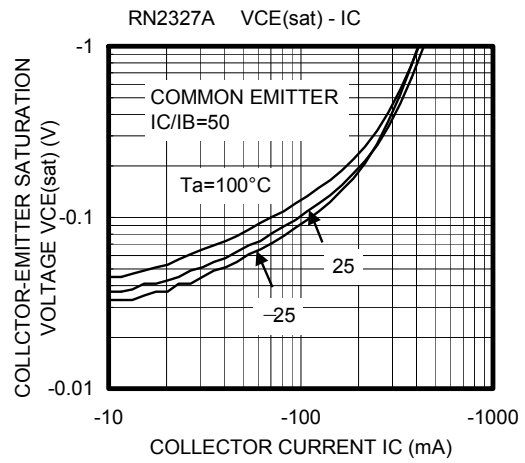
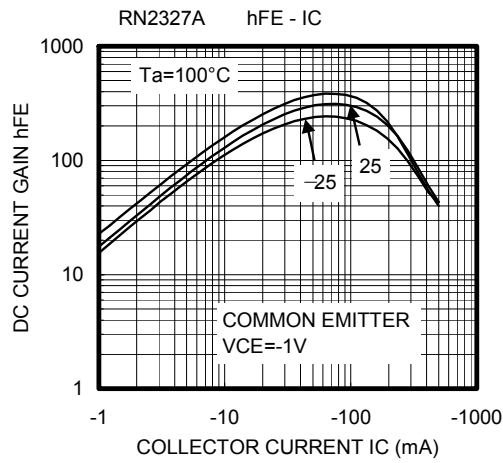
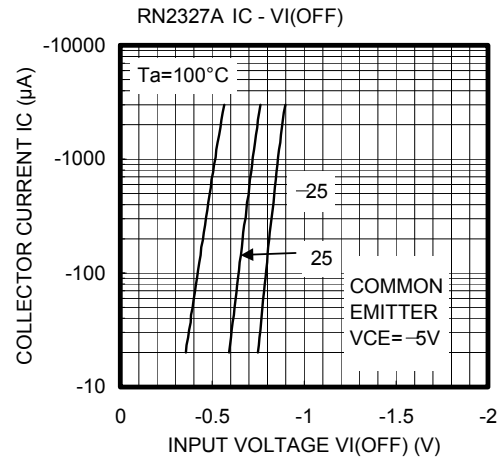
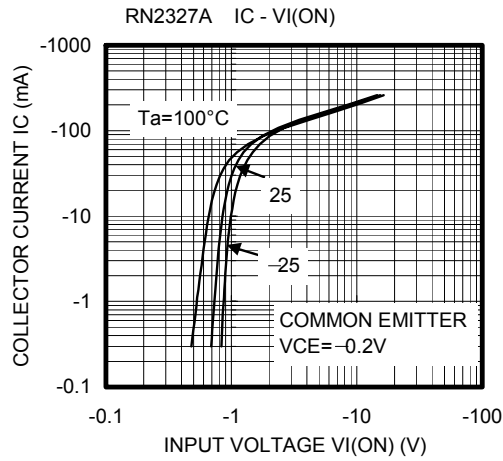


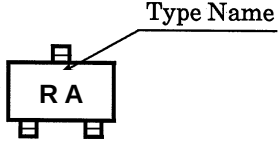
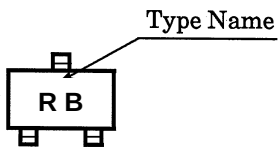
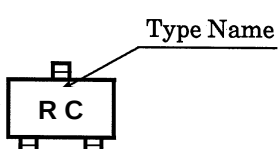
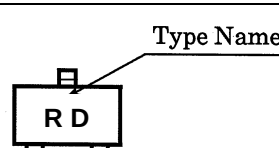
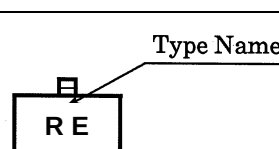
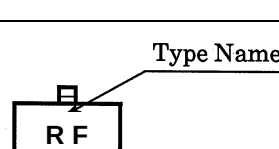
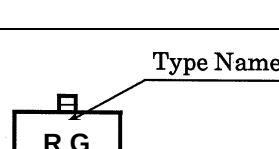










Type Name	Marking
RN2321A	
RN2322A	
RN2323A	
RN2324A	
RN2325A	
RN2326A	
RN2327A	

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